



austriamicrosystems 0.8 μm CMOS (CXQ)

Technology Description

Mixed Analog/Digital Process

- The 0.8 μm CMOS technology is a mixed mode process with two layers of metal and a high resistive poly.
- Operating Voltage [V]: 2.5-5.5

General Characteristics

- p substrate
- twin-well CMOS

Layout Rules

- Minimum electrical gate length : 0.8 μm for both PMOS and NMOS
- Polysilicon pitch : 1.7 μm
- Metal 1 pitch : 2.1 μm
- Metal 2 pitch : 2.3 μm

Thin Oxide Poly/Poly Capacitor

- Double poly capacitor
- High value : 0.86 fF/ μm^2
- High resistive Poly: 1.2 kOhm/square

Standard Cell Libraries

Digital Library

- Characterised at 5 V and 3.3 V operation
- Core cells optimized for synthesis
- I/O cells (pad and core limited)
- Maximum Junction temperature 150 deg C
- VHDL/Vital

Analog Library

- Not available through EUROPRACTICE.

- Available directly from austriamicrosystems. EUROPRACTICE can provide the contact address.